P4B60HP2F

Power MOSFETs
600V, 4A, N-channel

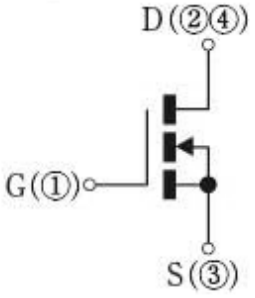
Feature

- N-channel
- SMD
- High Voltage
- High Speed
- Low Capacitance
- High Avalanche Durability, High di/dt Durability
- Pb free terminal
- RoHS:Yes

OUTLINE

Package (House Name): FB
Package (JEDEC Code): TO-252AA

Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel tempertature	Tch		150	°C
Drain-source voltage	V_{DSS}		600	V
Gate-source voltage	V_{GSS}		±30	V
Continuous drain current(DC)	I_D		4	A
Continuous drain current(Peak)	I_{DP}	Pulse width 10μs, duty=1/100	16	A
Continuous source current(DC)	Is		4	A
Total power dissipation	P_T		70	W
Repetitive avalanche current	I_{AR}	Starting Tch=25°C Tch≦150°C	4	A
Single avalanche energy	E_{AS}	Starting Tch=25°C Tch≦150°C	40	mJ
Repetitive avalanche energy	E_{AR}	Starting Tch=25°C Tch≦150°C	4	mJ
Drain - source diode di/dt strength	di/dt	Is=4A, Tc=25°C	350	A/μs

※ :See the original Specifications

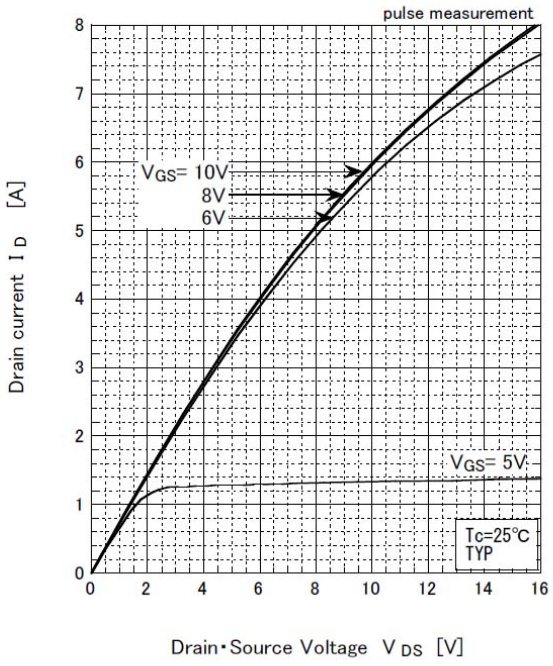
Electrical Characteristics (unless otherwise specified : Tc=25°C)

Item	Symbol	Conditions	Ratings			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	ID=1mA, VGS=0V	600			V
Zero gate voltage drain current	I_{DSS}	VDS=600V, VGS=0V			100	μA
Gate-source leakage current	I_{GSS}	VGS=±25V, VDS=0V			±10	μA
Forward transconductance	g_{fs}	ID=2A, VDS=10V	2.5	5		S
Static drain-source on-state resistance	$R_{DS(ON)}$	ID=2A, VGS=10V		1.6	1.9	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	2	3.25	4.5	V
Source-drain diode forward voltage	V_{SD}	IS=2A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case			1.78	°C/W
Total gate charge	Qg	VDD=400V, VGS=10V, ID=4A		13		nC
Input capacitance	Ciss	VDS=50V, VGS=0V, f=1MHz		520		pF
Reverce transfer capacitnce	Crss	VDS=50V, VGS=0V, f=1MHz		5		pF
Output capacitance	Coss	VDS=50V, VGS=0V, f=1MHz		51		pF
Turn-on delay time	td(on)	ID=2A, RL=75Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		13		ns
Rise time	tr	ID=2A, RL=75Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		26		ns
Turn-off delay time	td(off)	ID=2A, RL=75Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		54		ns
Fall time	tf	ID=2A, RL=75Ω, VDD=150V, Rg=50Ω, VGS(+)=10V, VGS(-)=0V		28		ns
Diode reverse recovery time	trr	IF=4A, VGS=0V, -di/dt=100A/μs		75		ns

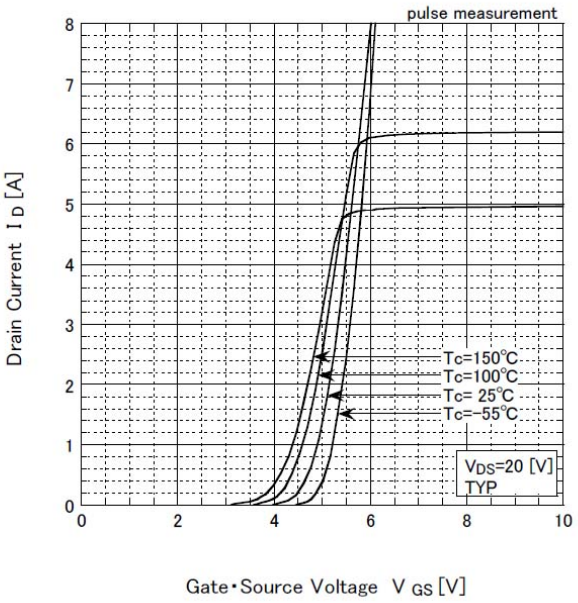
※ ：See the original Specifications

CHARACTERISTIC DIAGRAMS

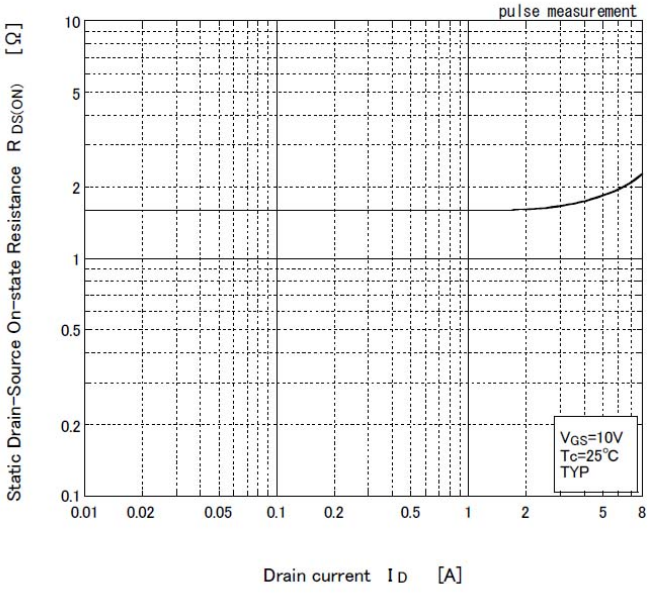
Typical Output Characteristics



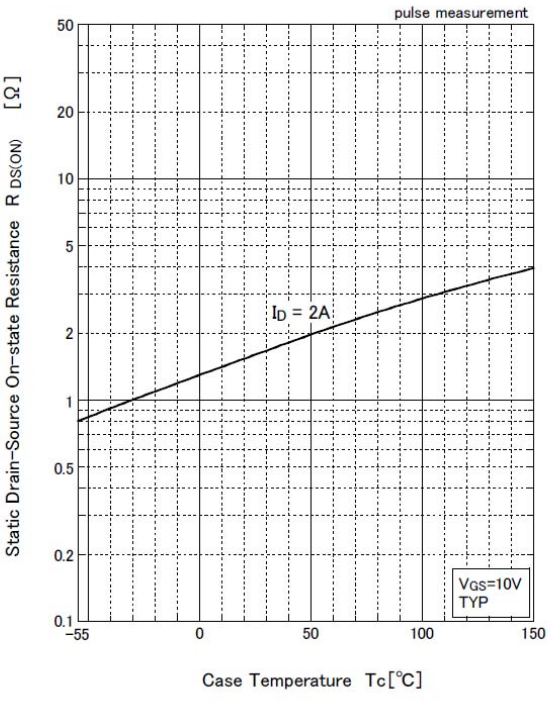
Transfer Characteristics



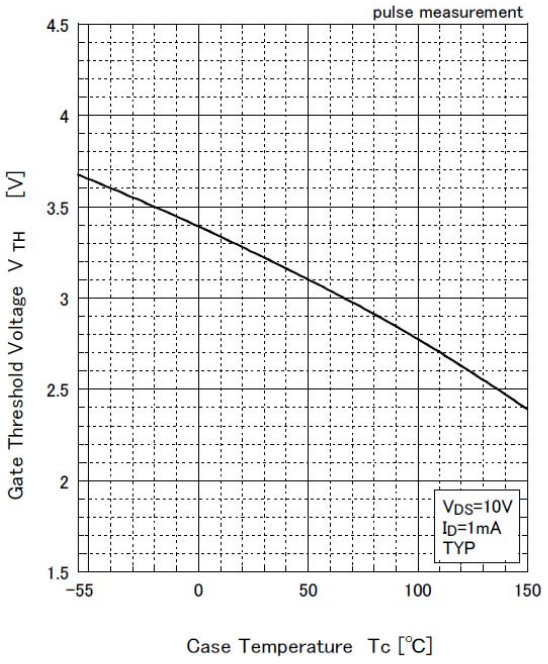
Static Drain-Source On-state Resistance vs Drain Current



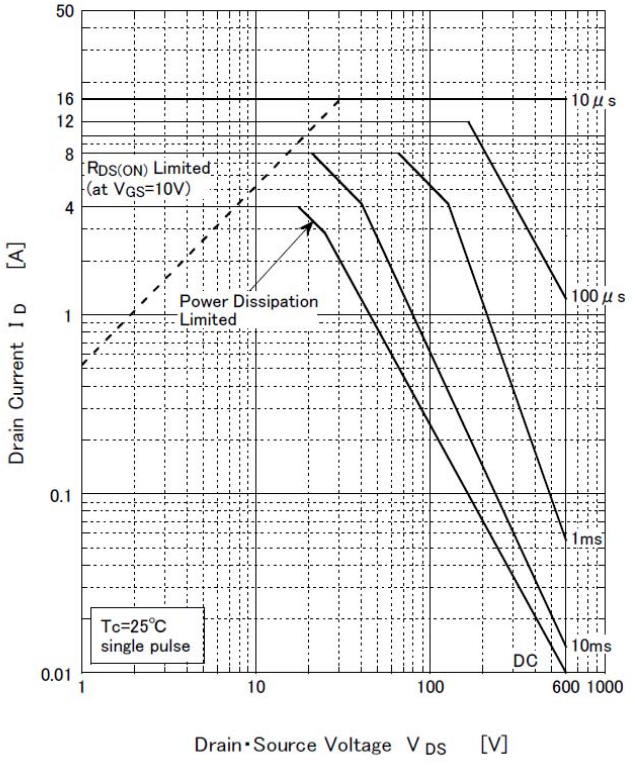
Static Drain-Source On-state Resistance vs Case Temperature

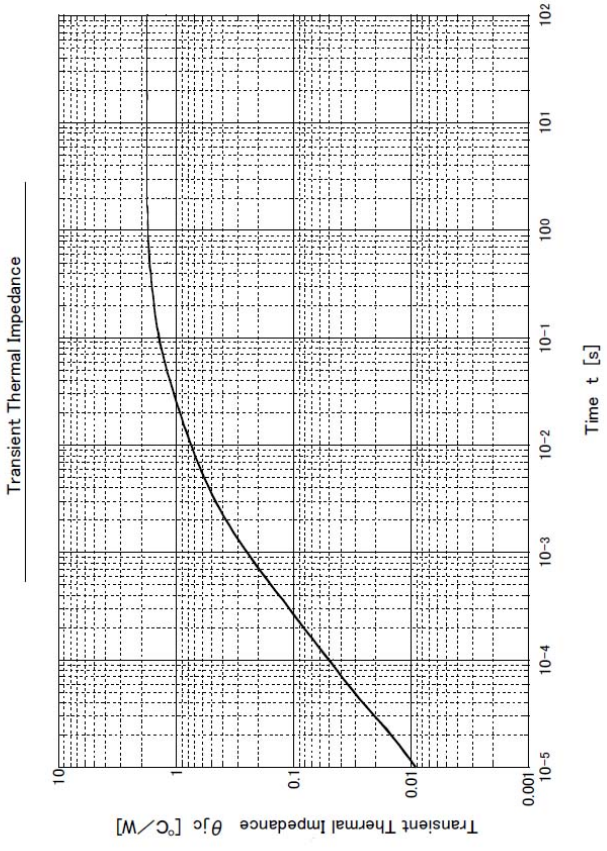


Gate Threshold Voltage
vs Case Temperature

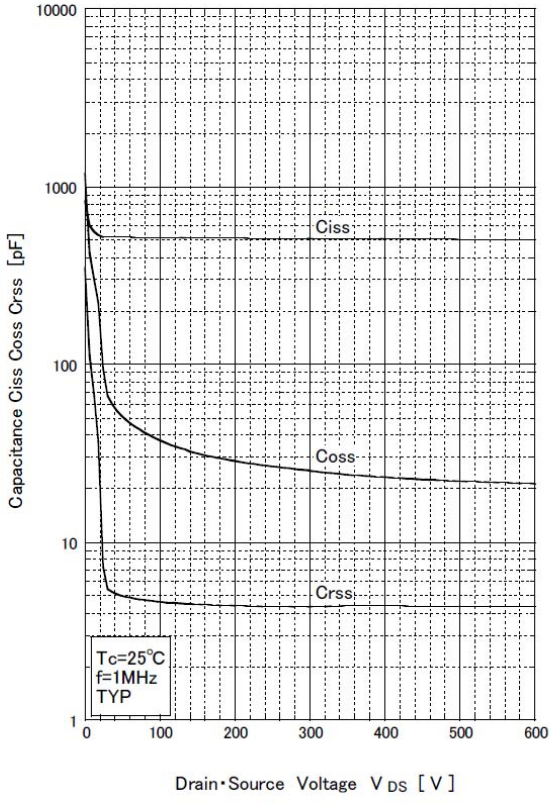


Safe Operating Area

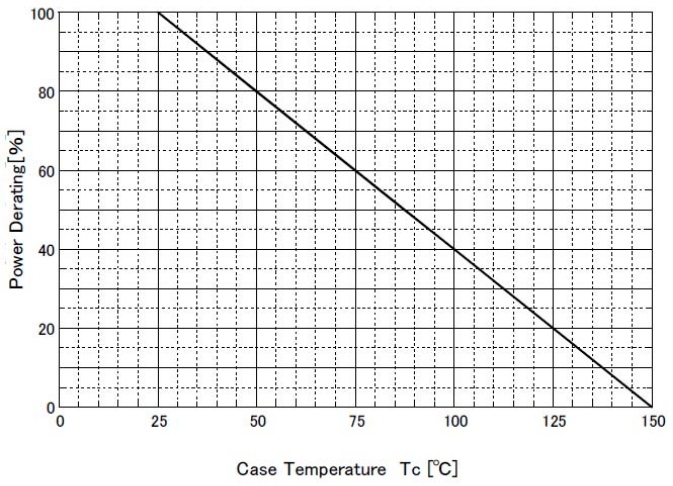




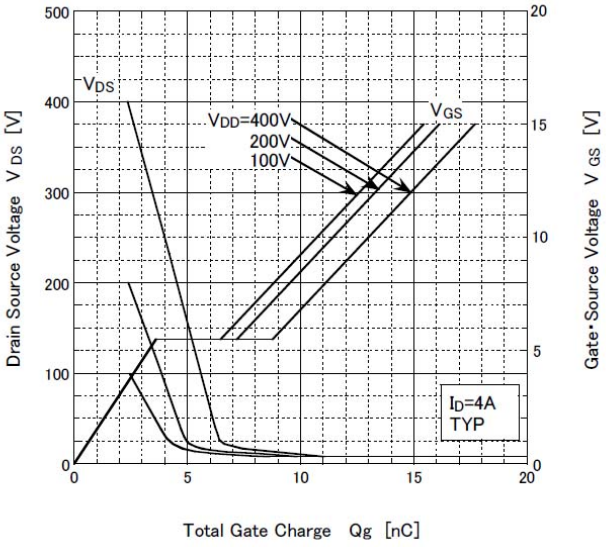
Capacitance Characteristics



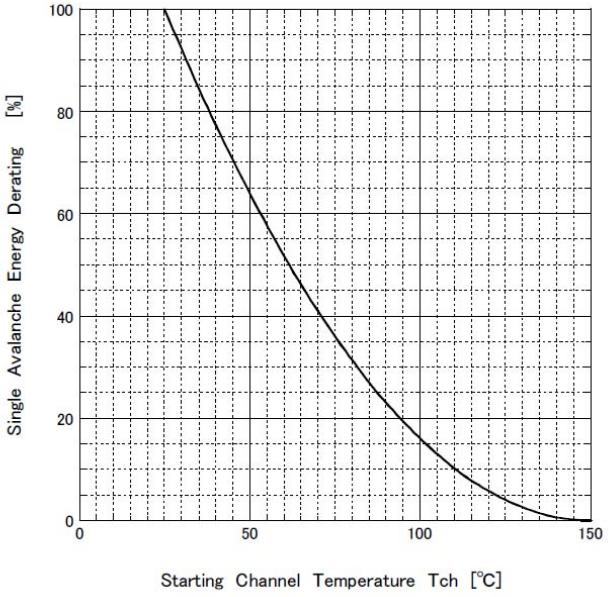
Power Derating - Case Temperature



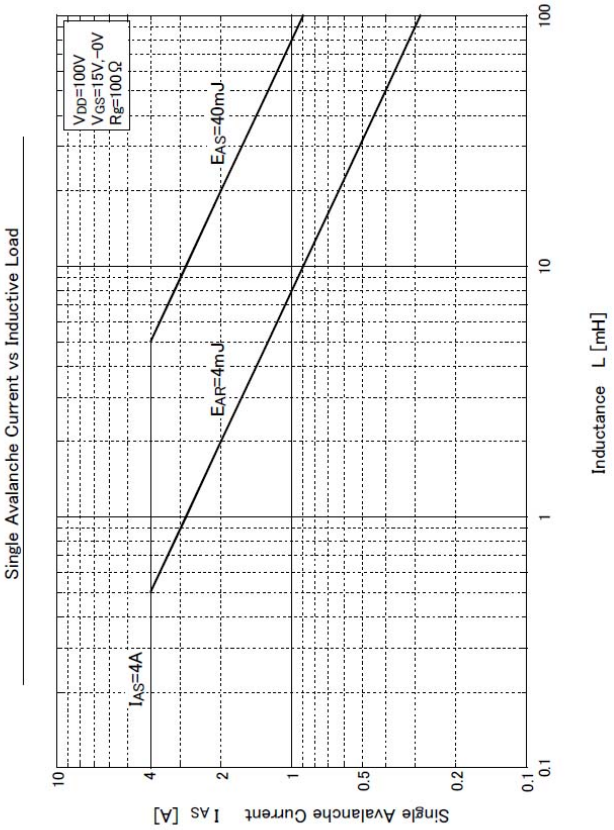
Gate Charge Characteristics



Single Avalanche Energy Derating
vs Channel Temperature



Single Avalanche Current vs Inductive Load

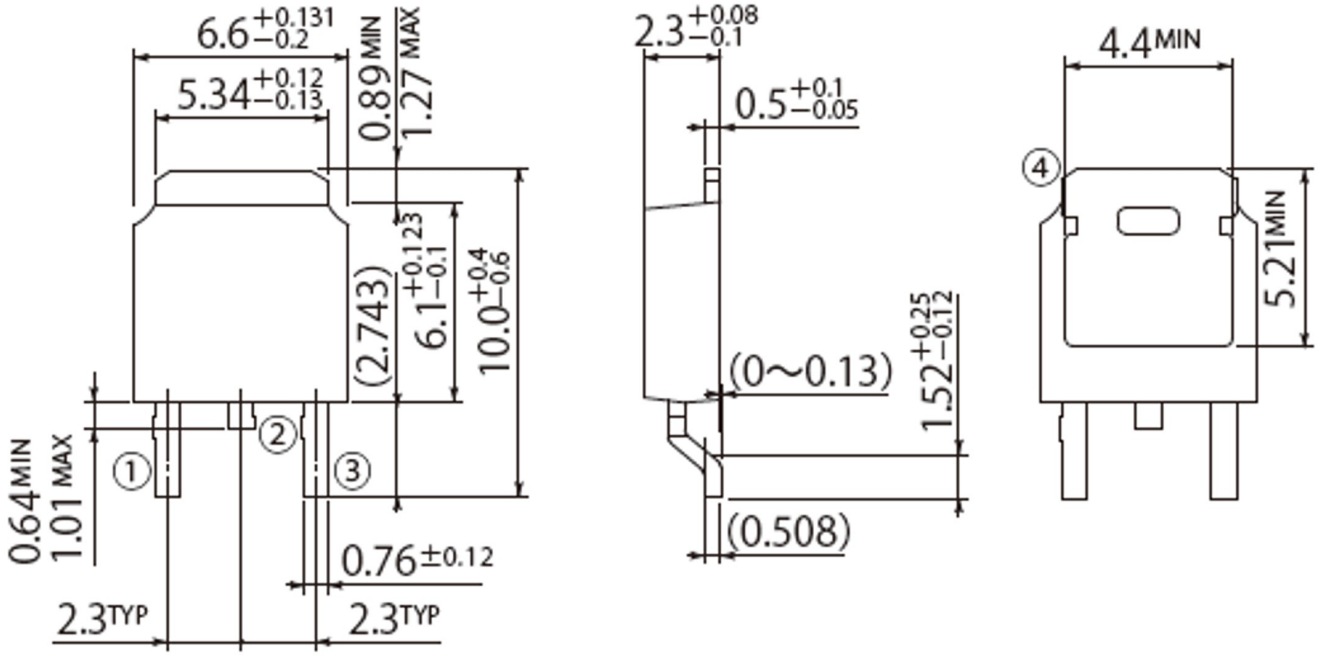


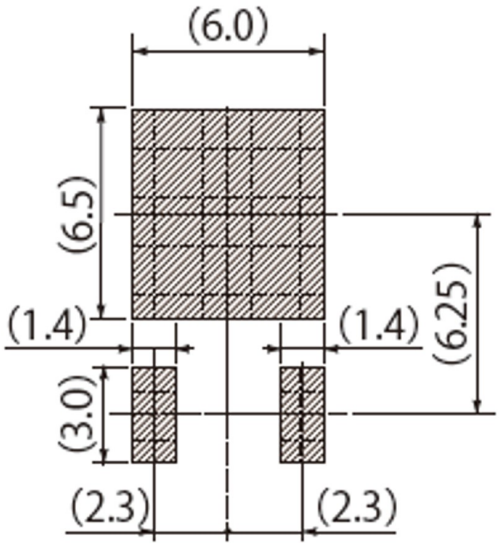
Outline Dimensions

unit:mm

G2

JEDEC Code	TO-252AA
JEITA Code	–
House Name	FB





Referential Soldering Pad

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